

ABSTRACT

Provides a semiconductor that enables to suppress deformation of the opening portions due to thermal expansion and contraction and to improve production yield and reliability wiring, and a method of fabricating the same. A first conductive layer and a second conductive layer are formed on a substrate. An insulation film is formed on upper surfaces of the first and second conductive layers and has a plurality of first opening portions to expose either the first or second conductive layer and a plurality of second opening portions to expose neither the first nor the second conductive layer. The second opening portions are formed between the first opening portions. A third conductive layer formed on an upper surface of the insulation film and has an electrical connection between the first and second conductive layers through the first opening portions.

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